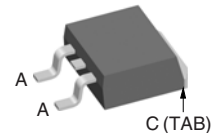


# Fast Recovery Epitaxial Diode (FRED)

$V_{RRM} = 600 \text{ V}$   
 $I_{FAVM} = 37 \text{ A}$   
 $t_{rr} = 35 \text{ ns}$

$V_{RSM}$	$V_{RRM}$	Type
V	V	
600	600	DSEI 36-06AS


**TO-263 AB**


A = Anode, C = Cathode, TAB = Cathode

Symbol	Test Conditions	Maximum Ratings	
$I_{FRMS}$	$T_{VJ} = T_{VJM}$	70	A
$I_{FAVM}$ ①	$T_C = 85^\circ\text{C}$ ; rectangular, $d = 0.5$	37	A
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	375	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	300	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	320	A
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	260	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	280	A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	450	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine	420	$\text{A}^2\text{s}$
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine	340	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine	320	$\text{A}^2\text{s}$
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{VJM}$		150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	125	W
Weight		2	g

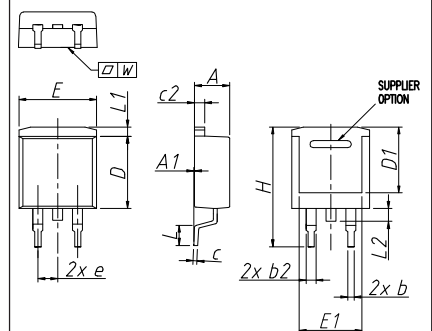
**Features**

- International standard surface mount package JEDEC TO-263 AB
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
$I_R$	$T_{VJ} = 25^\circ\text{C}$	$V_R = V_{RRM}$	100 $\mu\text{A}$
	$T_{VJ} = 25^\circ\text{C}$	$V_R = 0.8 \cdot V_{RRM}$	50 $\mu\text{A}$
	$T_{VJ} = 125^\circ\text{C}$	$V_R = 0.8 \cdot V_{RRM}$	7 mA
$V_F$	$I_F = 37 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$		1.4 V
	$T_{VJ} = 25^\circ\text{C}$		1.6 V
$V_{T0}$	For power-loss calculations only		1.01 V
$r_T$	$T_{VJ} = T_{VJM}$		7.1 $\text{m}\Omega$
$R_{thJC}$			1.0 K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 100 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	35	50 ns
$I_{RM}$	$V_R = 350 \text{ V}$ ; $I_F = 30 \text{ A}$ ; $-di_F/dt = 240 \text{ A}/\mu\text{s}$ $L \leq 0.05 \mu\text{H}$ ; $T_{VJ} = 100^\circ\text{C}$	10	11 A

①  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$

Data according to IEC 60747

**TO-263 AB Outline**


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.029
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
E	9.65	10.41	0.380	0.410
E1	6.22	8.20	0.245	0.323
e	2,54 BSC		0,100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
L2	1.02	1.52	0.040	0.060
W	typ. 0.02	0.040	typ. 0.0008	0.0016

All dimensions conform with and/or are within JEDEC standard.

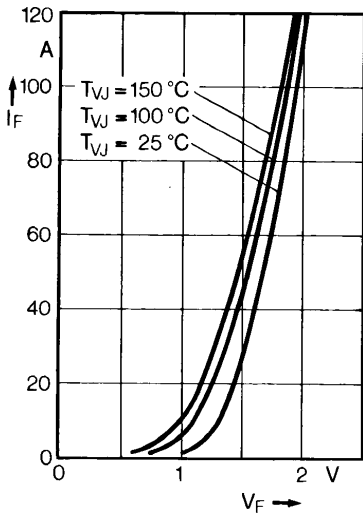


Fig. 1 Forward current versus voltage drop.

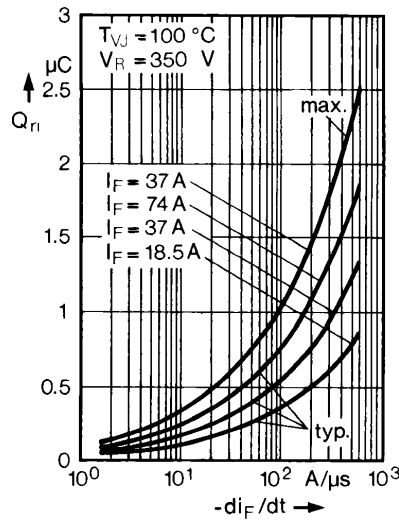


Fig. 2 Recovery charge versus  $-di_F/dt$ .

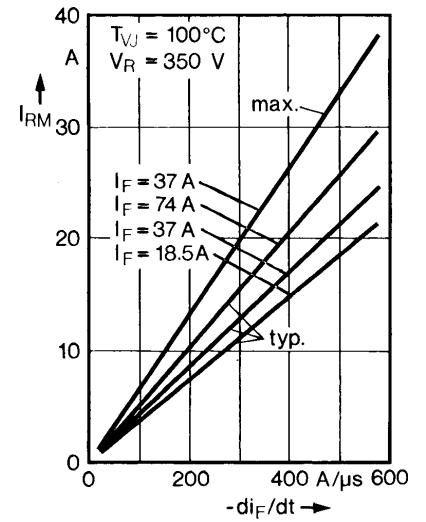


Fig. 3 Peak reverse current versus  $-di_F/dt$ .

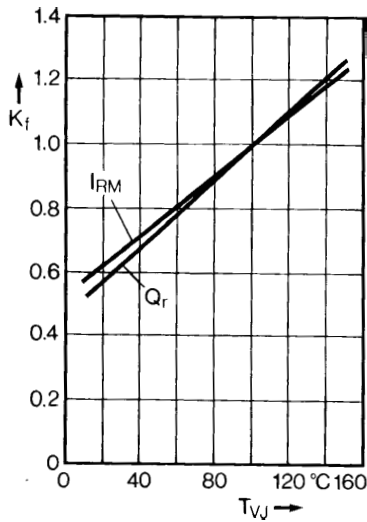


Fig. 4 Dynamic parameters versus junction temperature.

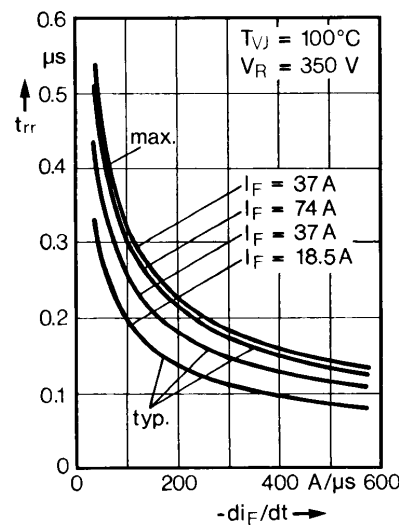


Fig. 5 Recovery time versus  $-di_F/dt$ .

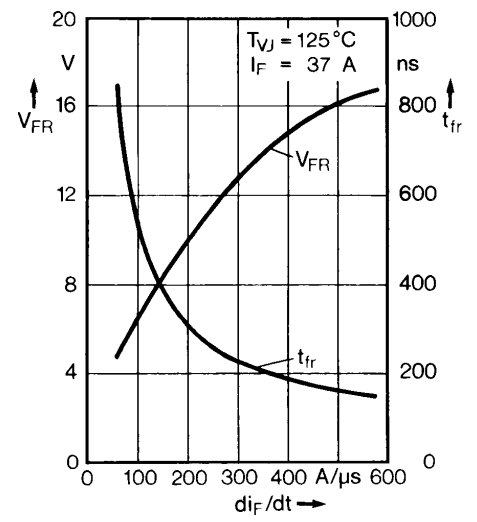


Fig. 6 Peak forward voltage versus  $di_F/dt$ .

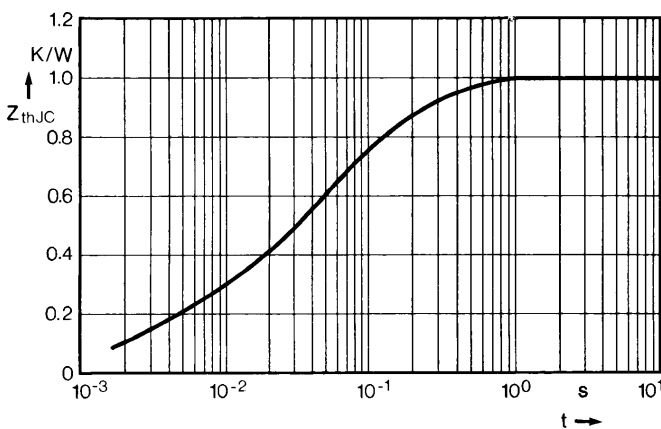


Fig. 7 Transient thermal impedance junction to case.